



东莞市华远电子有限公司

DONG GUAN SHI HUA YUAN ELECTRON CO.,LTD.

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TO-92 Plastic-Encapsulate Transistors

2SC2120

TRANSISTOR (NPN)

FEATURE

Power dissipation

P_{CM} : 0.6 W ($T_{amb}=25$)

Collector current

I_{CM} : 0.8 A

Collector-base voltage

$V_{(BR)CBO}$: 35 V

Operating and storage junction temperature range

T_{stg} : -55 to +150

T_J : 150

TO—92

1.EMITTER

2. COLLECTOR

3. BASE



ELECTRICAL CHARACTERISTICS ($T_{amb}=25$ unless otherwise specified)

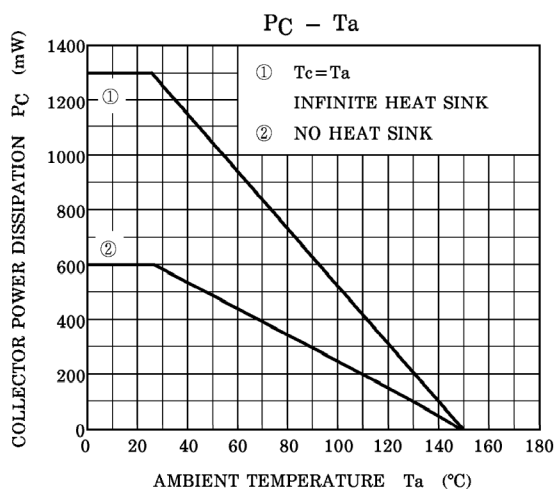
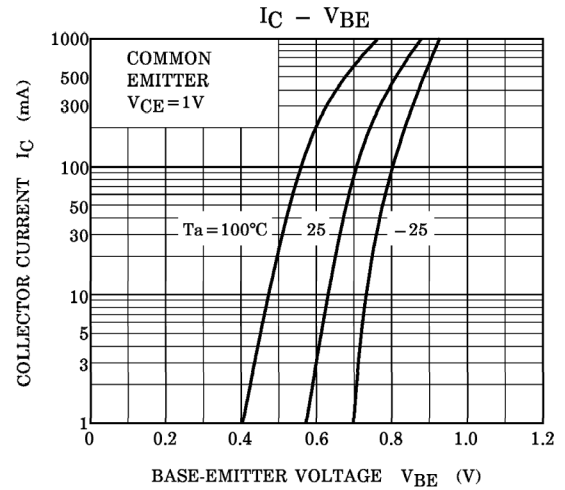
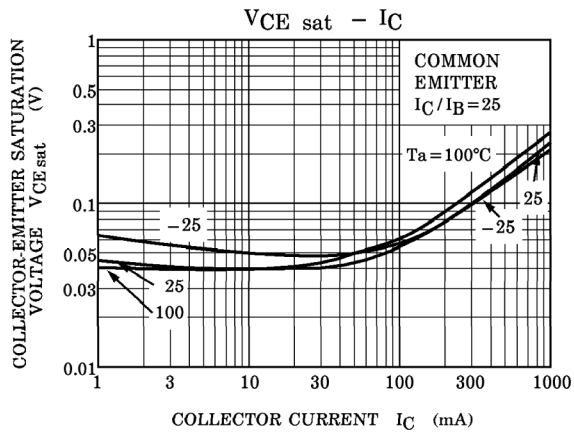
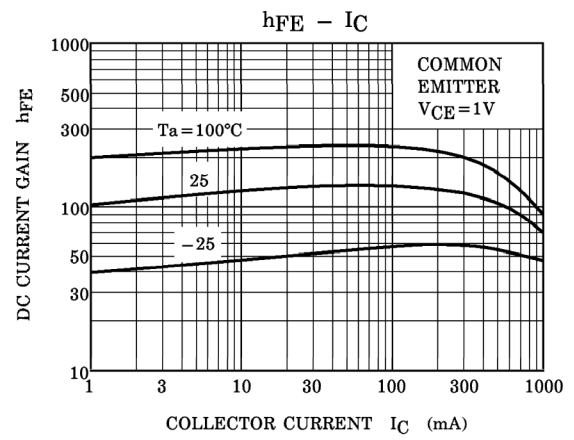
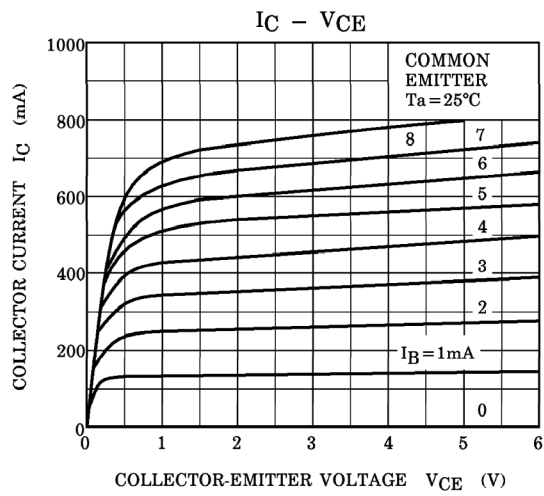
Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=0.1mA$, $I_E=0$	35			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=10mA$, $I_B=0$	30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=0.1mA$, $I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=35V$, $I_E=0$			0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE}=25V$, $I_B=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5V$, $I_C=0$			0.1	μA
DC current gain	h_{FE}	$V_{CE}=1V$, $I_C=100mA$	100		320	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=500mA$, $I_B=20mA$			0.5	V
Base-emitter voltage	V_{BE}	$V_{CE}=1V$, $I_C=10mA$			0.8	V
Transition frequency	f_T	$V_{CE}=5V$, $I_C=10mA$	100			MHz

CLASSIFICATION OF h_{FE}

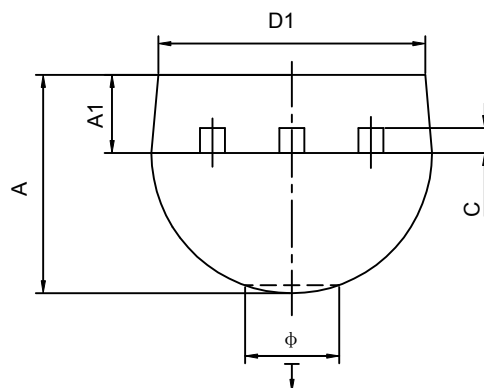
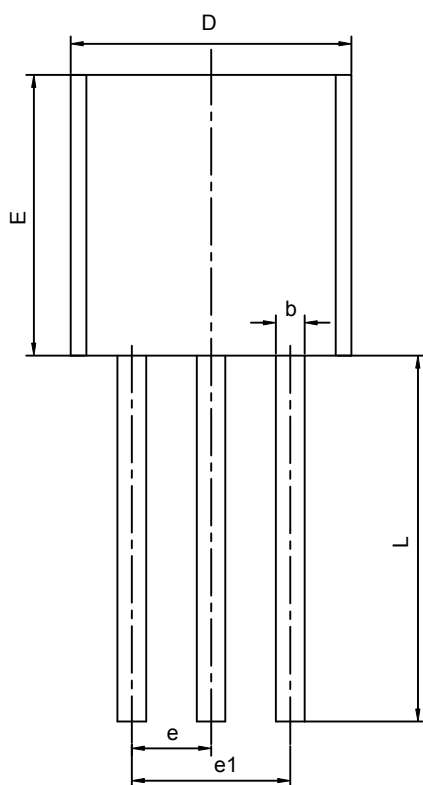
Rank	O	Y
Range	100-200	160-320

Typical Characteristics

2SC2120



TO-92 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	3.300	3.700	0.130	0.146
A1	1.100	1.400	0.043	0.055
b	0.380	0.550	0.015	0.022
c	0.360	0.510	0.014	0.020
D	4.400	4.700	0.173	0.185
D1	3.430		0.135	
E	4.300	4.700	0.169	0.185
e	1.270TYP		0.050TYP	
e1	2.440	2.640	0.096	0.104
L	14.100	14.500	0.555	0.571
Ö		1.600		0.063
\downarrow	0.000	0.380	0.000	0.015